P-Channel Enhancement-Mode Vertical DMOS FETs

Ordering Information

BV_{DSS} / BV_{DGS}	$R_{DS(ON)}$ (max)	$I_{D(ON)}$ (min)	Order Number / Package		
			TO-92	TO-243AA*	Die†
-30V	0.6Ω	-4.0A	VP3203N3	VP3203N8	VP3203ND

*Same as SOT-89. Product supplied on 2000 piece carrier tape reels.

† MIL visual screening available.

Product marking for TO-243AA:

VP2L∗

Where ∗ = 2-week alpha date code

Features

- ❏ Free from secondary breakdown
- ❏ Low power drive requirement
- ❏ Ease of paralleling
- ❏ Low C_{ISS} and fast switching speeds
- ❏ Excellent thermal stability
- ❏ Integral Source-Drain diode
- ❏ High input impedance and high gain
- ❏ Complementary N- and P-channel devices

Applications

- ❏ Motor controls
- ❏ Converters
- ❏ Amplifiers
- ❏ Switches
- ❏ Power supply circuits
- ❏ Drivers (relays, hammers, solenoids, lamps, memories, displays, bipolar transistors, etc.)

Advanced DMOS Technology

These enhancement-mode (normally-off) transistors utilize a vertical DMOS structure and Supertex's well-proven silicon-gate manufacturing process. This combination produces devices with the power handling capabilities of bipolar transistors and with the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, these devices are free from thermal runaway and thermally-induced secondary breakdown.

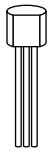
Supertex's vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

Absolute Maximum Ratings

Drain-to-Source Voltage	BV_{DSS}
Drain-to-Gate Voltage	BV_{DGS}
Gate-to-Source Voltage	± 20V
Operating and Storage Temperature	-55°C to +150°C
Soldering Temperature*	300°C

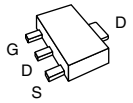
* Distance of 1.6 mm from case for 10 seconds.

Package Options



S G D

TO-92



TO-243AA
(SOT-89)

Note: See Package Outline section for dimensions.

11/12/01

Thermal Characteristics

Package	I_D (continuous)*	I_D (pulsed)	Power Dissipation @ T_A = 25°C	θ_{jc} °C/W	θ_{ja} °C/W	I_{DR}*	I_{DRM}
TO-92	-0.65A	-4.0A	0.74W	125	170	-0.65A	-4.0A
TO-243AA	-1.1A	-4.0A	1.6W†	15	78†	-1.1A	-4.0A

* I_D (continuous) is limited by max rated T_j.

† Mounted on FR5 board, 25mm x 25mm x 1.57mm. Significant P_D increase possible on ceramic substrate.

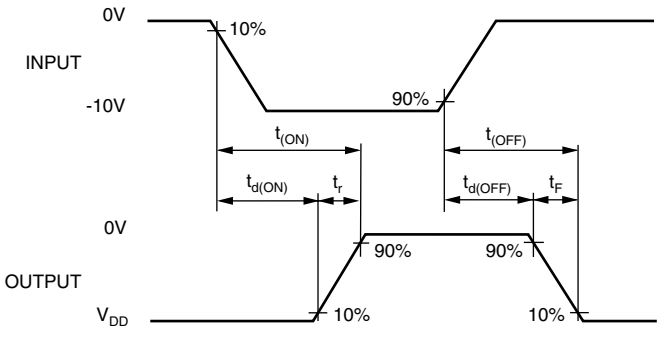
Electrical Characteristics (@ 25°C unless otherwise specified)

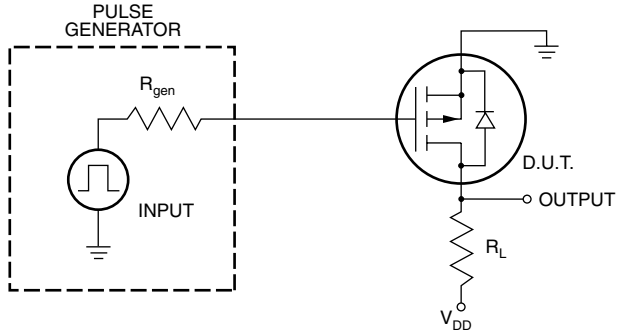
Symbol	Parameter		Min	Typ	Max	Unit	Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage		-30			V	V_{GS} = 0V, I_D = -10mA
$V_{GS(th)}$	Gate Threshold Voltage		-1.0		-3.5	V	V_{GS} = V_{DS}, I_D = -10mA
$\Delta V_{GS(th)}$	Change in $V_{GS(th)}$ with Temperature				-5.5	mV/°C	V_{GS} = V_{DS}, I_D = -10mA
I_{GSS}	Gate Body Leakage			-1.0	-100	nA	V_{GS} = ±20V, V_{DS} = 0V
I_{DSS}	Zero Gate Voltage Drain Current				-10	µA	V_{GS} = 0V, V_{DS} = Max Rating
					-1	mA	V_{GS} = 0V, V_{DS} = 0.8 Max Rating T_A = 125°C
$I_{D(ON)}$	ON-State Drain Current			-14		A	V_{GS} = -10V, V_{DS} = -5V
$R_{DS(ON)}$	Static Drain-to-Source ON-State Resistance	TO-92			1.0	Ω	V_{GS} = -4.5V, I_D = -1.5A
		SOT-89			1.0	Ω	V_{GS} = -4.5V, I_D = -0.75A
		TO-92			0.6	Ω	V_{GS} = -10V, I_D = -3A
		SOT-89			0.6	Ω	V_{GS} = -10V, I_D = -1.5A
$\Delta R_{DS(ON)}$	Change in $R_{DS(ON)}$ with Temperature				1.0	%/°C	V_{GS} = -10V, I_D = -1.5A
G_{FS}	Forward Transconductance		1.0	2.0		℧	V_{DS} = -25V, I_D = -2A
C_{ISS}	Input Capacitance			200	300	pF	V_{GS} = 0V, V_{DS} = -25V f = 1 MHz
C_{OSS}	Common Source Output Capacitance			100	120		
C_{RSS}	Reverse Transfer Capacitance			45	60		
$t_{d(ON)}$	Turn-ON Delay Time				10	ns	V_{DD} = -25V I_D = -2A R_{GEN} = 10Ω
t_r	Rise Time				15		
$t_{d(OFF)}$	Turn-OFF Delay Time				25		
t_f	Fall Time				25		
V_{SD}	Diode Forward Voltage Drop				-1.6	V	V_{GS} = 0V, I_{SD} = -1.5A
t_{rr}	Reverse Recovery Time			300		ns	V_{GS} = 0V, I_{SD} = -1A

Notes:

1. All D.C. parameters 100% tested at 25°C unless otherwise stated. (Pulse test: 300µs pulse, 2% duty cycle.)
2. All A.C. parameters sample tested.

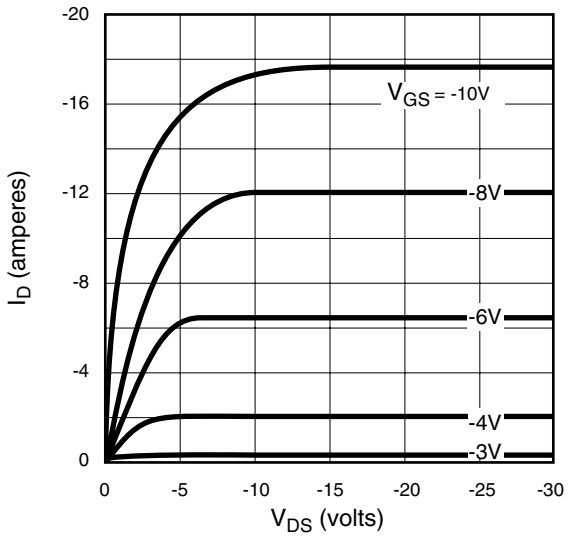
Switching Waveforms and Test Circuit



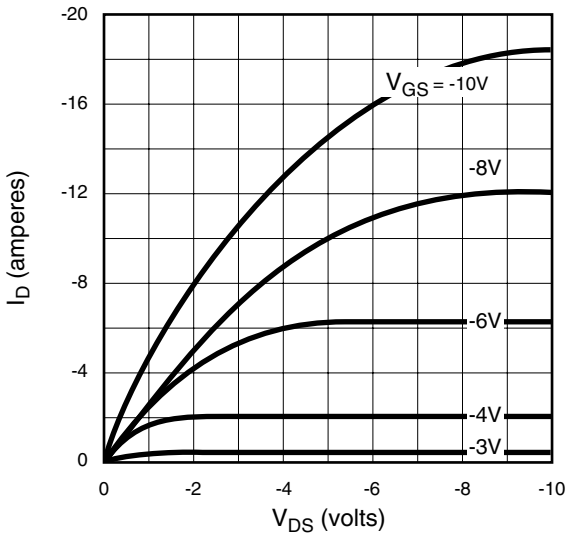


Typical Performance Curves

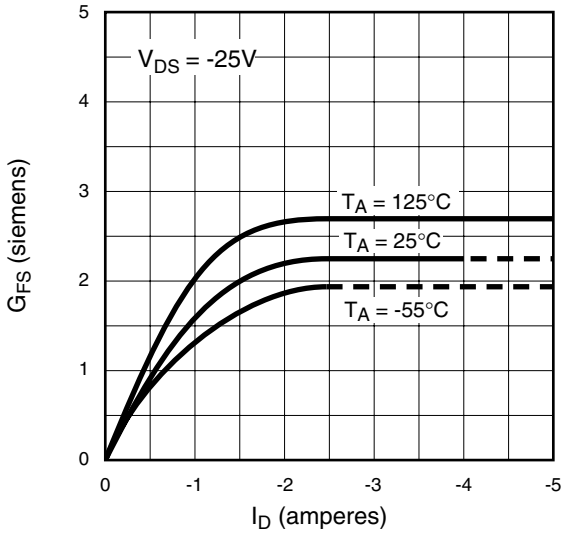
Output Characteristics



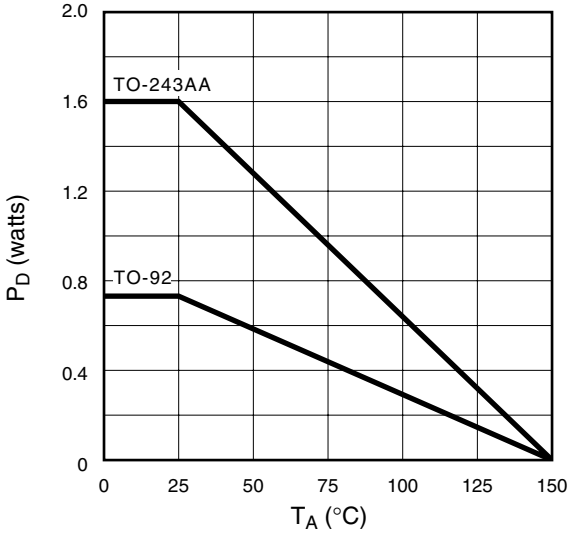
Saturation Characteristics



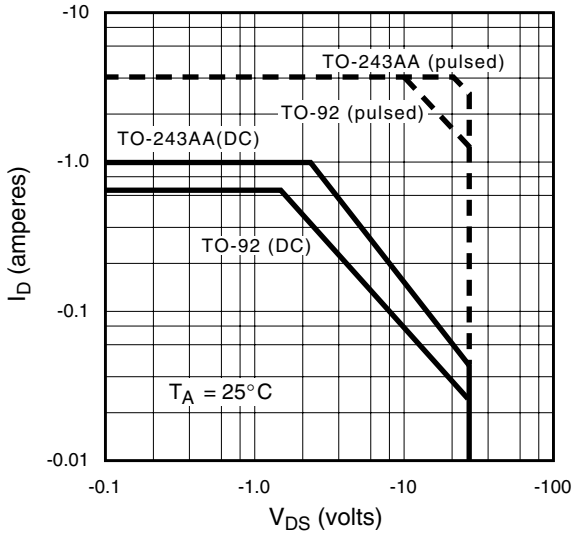
Transconductance vs. Drain Current



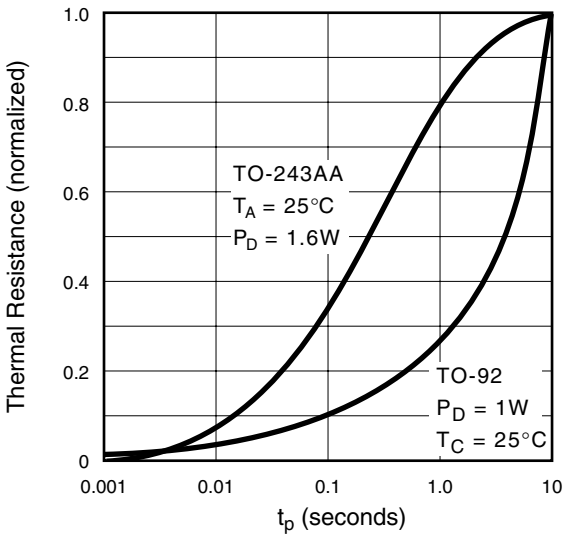
Power Dissipation vs. Temperature



Maximum Rated Safe Operating Area

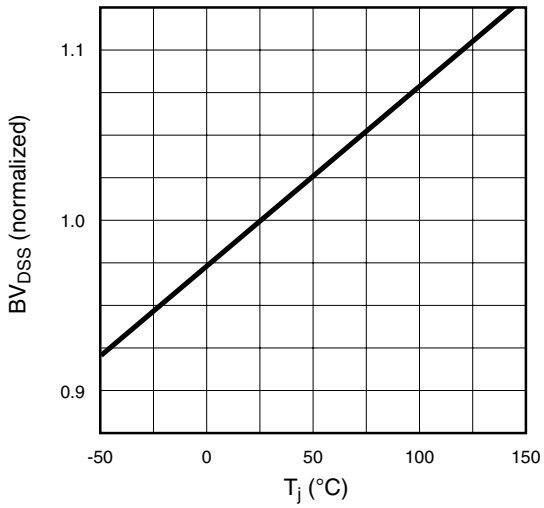


Thermal Response Characteristics

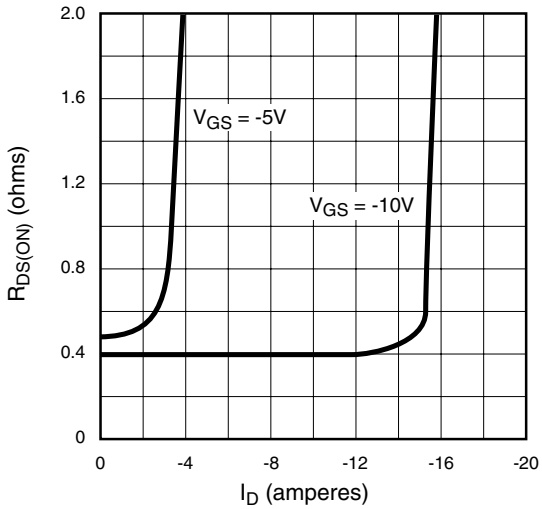


Typical Performance Curves

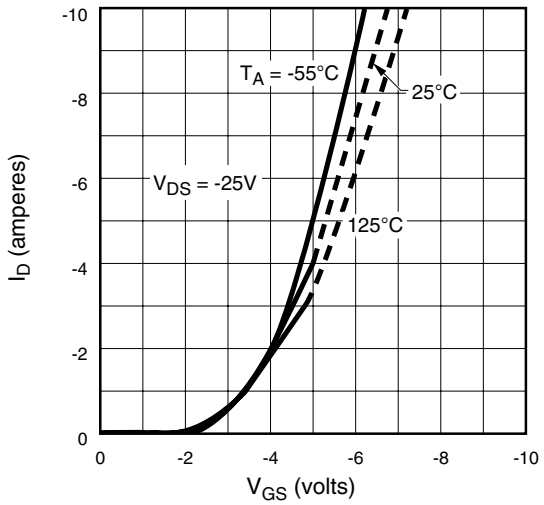
BV$_{DSS}$ Variation with Temperature



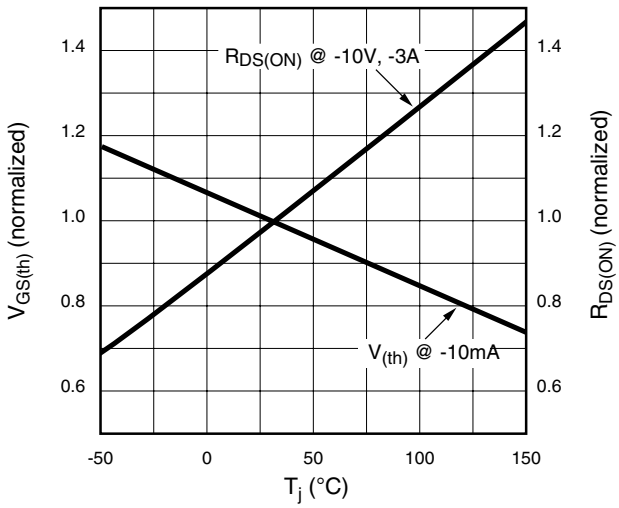
On-Resistance vs. Drain Current



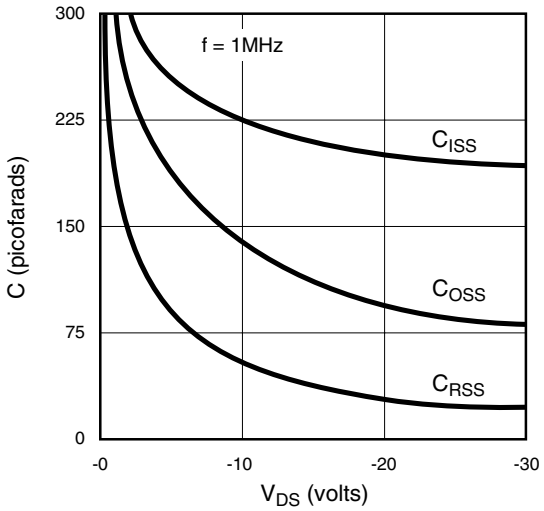
Transfer Characteristics



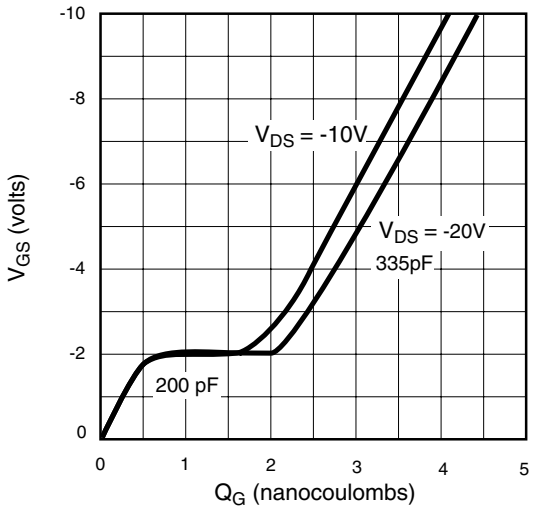
V$_{(th)}$ and R$_{DS}$ Variation with Temperature



Capacitance vs. Drain-to-Source Voltage



Gate Drive Dynamic Characteristics



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